

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSV)

# 2SK3342

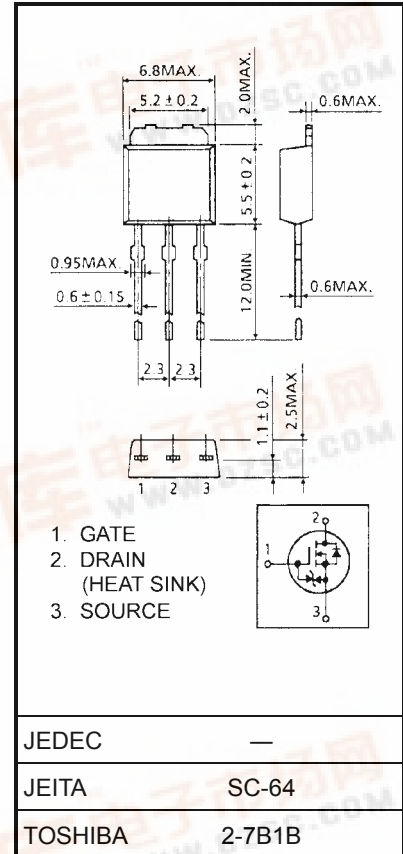
Switching Regulator Applications DC-DC Converter, and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance :  $R_{DS(ON)} = 0.8 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 4.5 S$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 250 V$ )
- Enhancement-mode :  $V_{th} = 1.5 \sim 3.5 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	250	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )		$V_{DGR}$	250	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	4.5	A
	Pulse (Note 1)	$I_{DP}$	18	A
Drain power dissipation ( $T_c = 25^\circ C$ )		$P_D$	20	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	51	mJ
Avalanche current		$I_{AR}$	4.5	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	2.0	mJ
Channel temperature		$T_{ch}$	150	$^\circ C$
Storage temperature range		$T_{stg}$	$-55 \sim 150$	$^\circ C$



Weight: 0.36 g (typ.)

## Thermal Characteristics

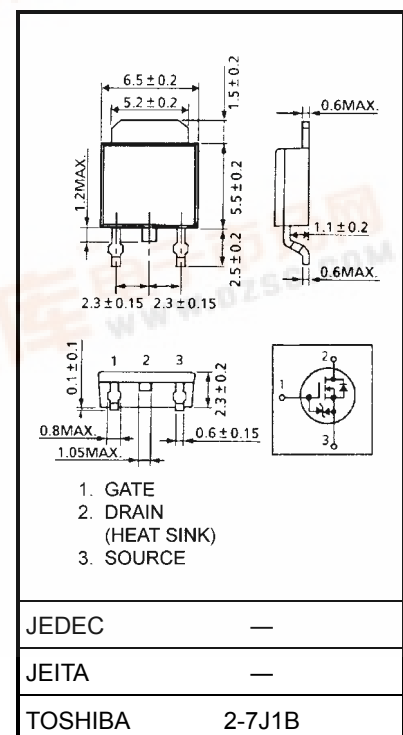
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	6.25	$^\circ C / W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	125	$^\circ C / W$

Note 1: Please use devices on condition that the channel temperature is below  $150^\circ C$ .

Note 2:  $V_{DD} = 50 V, T_{ch} = 25^\circ C$  (initial),  $L = 4.28 mH, R_G = 25 \Omega, I_{AR} = 4.5 A$

Note 3: Repetitive rating; Pulse width limited by maximum channel temperature.

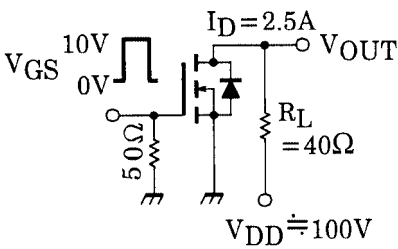
This transistor is an electrostatic sensitive device. Please handle with caution.



Weight: 0.36 g (typ.)



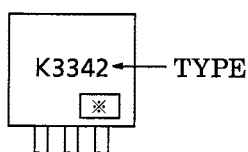
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	250	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$	—	0.8	1.0	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 2.5\text{ A}$	2.0	4.5	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	440	—	pF
Reverse transfer capacitance		$C_{rss}$		—	35	—	
Output capacitance		$C_{oss}$		—	120	—	
Switching time	Rise time	$t_r$	 <p><math>I_D = 2.5\text{ A}</math> <math>V_{GS} = 10\text{ V}, 0\text{ V}</math> <math>R_L = 40\Omega</math> <math>V_{DD} = 100\text{ V}</math> <math>50\Omega</math></p>	—	15	—	ns
	Turn-on time	$t_{on}$		—	20	—	
	Fall time	$t_f$		—	15	—	
	Turn-off time	$t_{off}$		Duty $\leq 1\%$ , $t_w = 10\mu\text{s}$	—	60	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$	—	10	—	nC
Gate-source charge		$Q_{gs}$		—	6	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	4	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	4.5	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	18	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 4.5\text{ A}, V_{GS} = 0\text{ V}$	—	—	-2.0	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 4.5\text{ A}, V_{GS} = 0\text{ V}$	—	110	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR} / dt = 100\text{ A} / \mu\text{s}$	—	0.47	—	$\mu\text{C}$

## Marking



※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)

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000707EAA

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